

GAE

GREAT AMERICAN ELECTROINCS

DM20-28

Silicon NPN high power UHF transistor DM20-28 is designed for common base wide band amplifier, driver, or oscillator applications in land and mobile and on-board radio systems.

Output Power: 20 Watt
Frequency Range: 400-1000 Mhz
Voltage: 28 V
Package Type: 3/8 Helicopter
Input Matched
Common Base Configuration
Emitter Ballast Resistors
Aluminum Metalization

Electrical Characteristics ($T_{CASE}=40^{\circ}C$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{out}	$f_o = 1000 \text{ Mhz}/V_{cc}=28V/P_{IN}=5.7W$	20			W
G_p	$f_o = 1000 \text{ Mhz}/V_{cc}=28V/P_{out}=20W$	5.5	9	10	dB
λ_c	$f_o = 1000 \text{ Mhz}/V_{cc}=28V/P_{out}=20W$	40	50		%

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

SYMBOL	PARAMETERS	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{EBO}	Emitter-Base Voltage	4	V
I_c	Continuous Collector Current	2.5	A
P_C	Collector Power Dissipation	27*	W
T_j	Junction Temperature	160	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	4.4	$^{\circ}C/W$

*For Dynamic Operation $T_{CASE} = 40^{\circ}C$